

isc Silicon NPN Power Transistor

2SD2551

DESCRIPTION

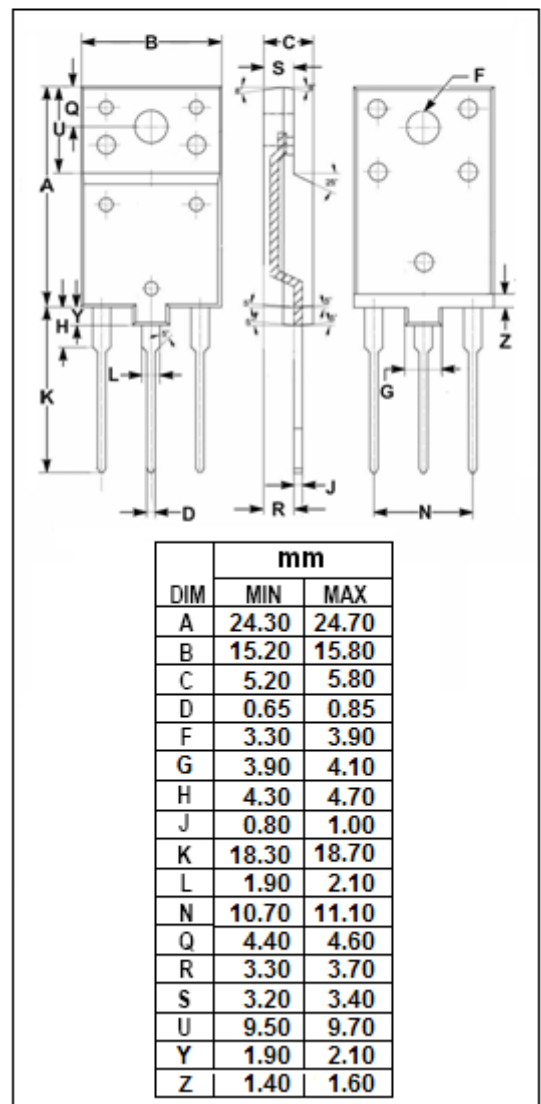
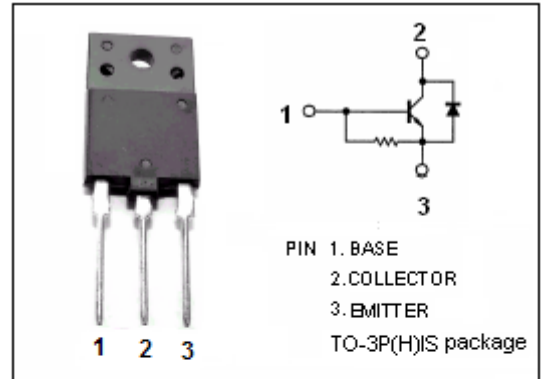
- High Breakdown Voltage-
: $V_{CBO} = 1700V$ (Min)
- High Switching Speed
- Low Saturation Voltage
- Built-in Damper Diode

APPLICATIONS

- Designed for color TV horizontal deflection applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1700	V
V_{CEO}	Collector-Emitter Voltage	600	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current- Continuous	5	A
I_{CM}	Collector Current- Pulse	10	A
I_B	Base Current- Continuous	2.5	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	50	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 300mA; I _C = 0	5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 0.8A			5.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 4A; I _B = 0.8A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 1700V; I _E = 0			1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0	66		200	mA
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 5V	8		28	
h _{FE-2}	DC Current Gain	I _C = 4A; V _{CE} = 5V	5		10	
V _{ECF}	C-E Diode Forward Voltage	I _F = 5A			2.0	V
f _T	Current-Gain—Bandwidth Product	I _C = 0.1A; V _{CE} = 10V		3		MHz
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} =1.0MHz		125		pF

Switching Times

t _s	Storage Time	I _{CP} = 4A, I _{B1(end)} = 0.8A, f _H = 15.75kHz			10	μs
t _f	Fall Time				1.0	μs